

1S1585~1S1588 Silicon Epitaxial Planar Type Diode

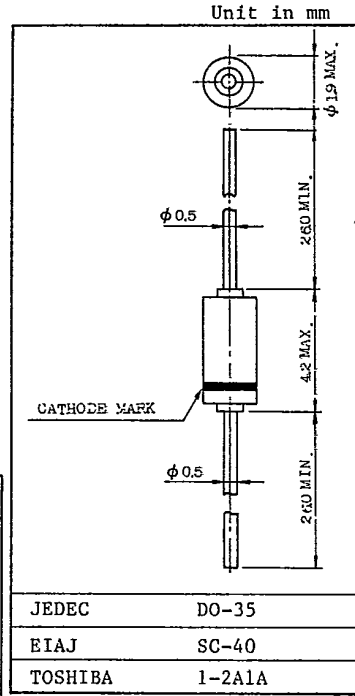
ULTRA HIGH SPEED SWITCHING APPLICATIONS.

FEATURES:

- Low Forward Voltage : $V_F=1.0V$ (Max.)
- Small Total Capacitance : $C_T=2pF$ (Max.)
- Fast Reverse Recovery Time : $T_{RR}=2ns$ (Max.)

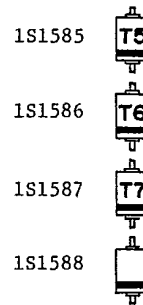
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	1S1585	V_{RM}	90	V
	1S1586		55	
	1S1587		35	
Reverse Voltage	1S1585	V_R	80	V
	1S1586		50	
	1S1587		30	
Maximum (Peak) Forward Current	1S1585	I_{FM}	480	mA
	1S1586		400	
	1S1587		360	
Average Forward Current	1S1585	I_O	150	mA
	1S1586		130	
	1S1587		120	



Weight : 0.14g

Marking



1S1585 ~ 1S1588

CHARACTERISTIC		SYMBOL	RATING	UNIT
Surge Current (1 sec)	1S1585	I _{FSM}	700	mA
	1S1586			
	1S1587		600	
	1S1588			
Power Dissipation		P	300	mW
Junction Temperature		T _j	175	°C
Storage Temperature Range		T _{stg}	-65 ~ 175	°C

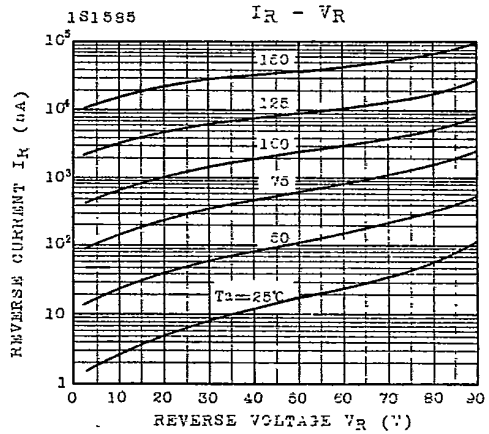
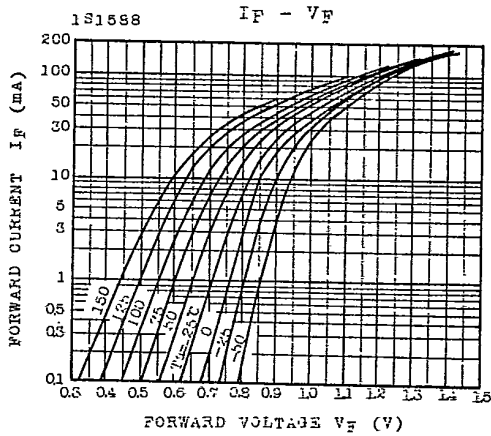
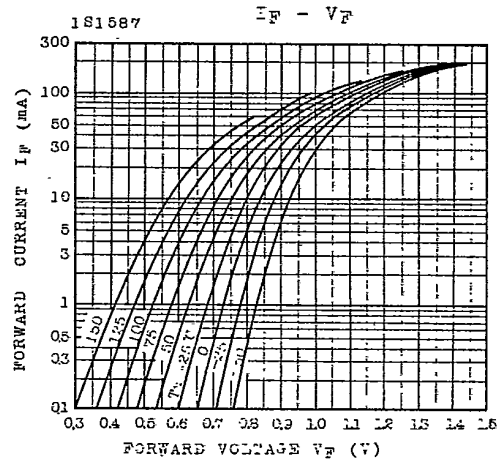
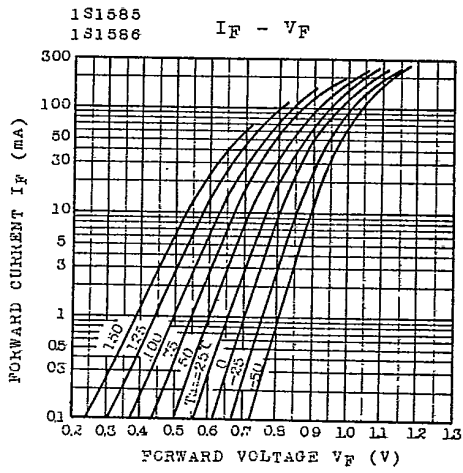
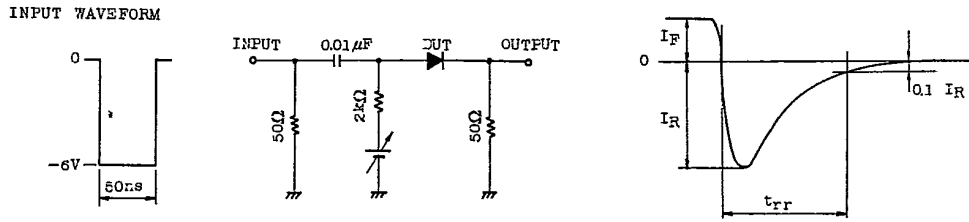
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	1S1585	V _F	I _F = 100mA	-	-	1.0	V
	1S1586					1.2	
	1S1587					1.3	
	1S1588						
Reverse Current	1S1585	I _R	V _R = 80V	-	-	0.5	μA
	1S1586		V _R = 50V				
	1S1587						
	1S1588		V _R = 30V				
Total Capacitance	1S1585	C _T	V _R = 0 f = 1MHz	-	-	2	pF
	1S1586					3	
	1S1587						
	1S1588						
Reverse Recovery Time	1S1585	t _{rr}	V _R = 6V I _F = 10mA R _L = 100Ω (Fig.)	-	-	2	ns
	1S1586					4	
	1S1587						
	1S1588						

TOSHIBA CORPORATION

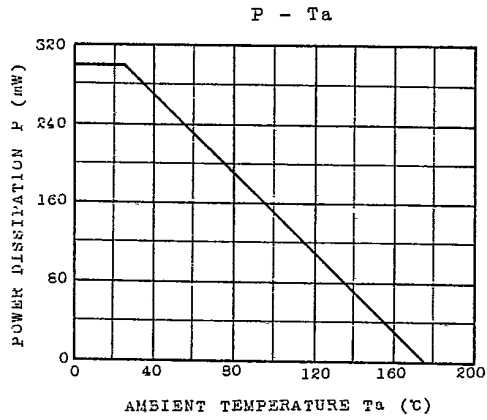
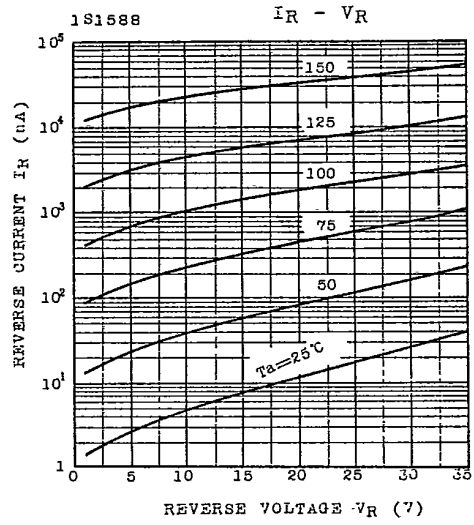
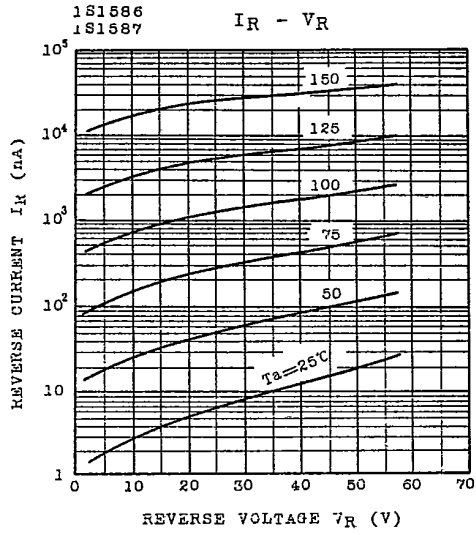
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Fig. t_{rr} TEST CIRCUIT



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